Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5	(US-20020053682-$ or US-20010005016-$ or US-20030132496-$).did. or (US-6534790-$).did. or (EP-1424734-$).did.	US-PGPUB; USPAT; EPO	OR	OFF	2005/11/14 09:16
L2	33	p-jfet	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:56
L3	119	jfet and algaas	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:56
L4	117	3 not 2	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 10:01
L5	7	"5159414"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 10:01
S88	7	(US-20040104404-$ or US-20030132496-$ or US-20020053682-$ or US-20010019131-$ or US-20010013604-$ or US-20010005016-$).did. or (EP-1424734-$).did.	US-PGPUB; EPO	OR	OFF	2005/11/09 08:47
S89	5	S88 and Ingaas adj channel	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 09:05
S90	1	jp-2001250939-$	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 09:04
S91	1	jp-2001250939-$	JPO; IBM_TDB	OR	OFF	2005/11/09 09:04
S94	408	(InP InGaP GaInP Ingaas GaAs) adj channel and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 12:46

S95	2	(InP InGaP GaInP Ingaas GaAs) adj channel and ((AlGaAs GaAlAs) and GaAs) near3 etch adj stop	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 10:14
S96	50	S94 and gate with p-type	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 09:10
S97	127	(InP InGaP GaInP Ingaas GaAs) with schottky adj layer	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:30
S98	19	(InP InGaP GaInP Ingaas GaAs) adj schottky adj layer	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 12:45
S99	74	S97 and GaAs near3 substrate	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:45
S100	41	S99 and @pd>"20011113"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:45
S101	11	S100 and p-type	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 11:59
S102	30	S100 not S101	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 12:40
S103	1	pj-hfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:40
S104	314	p-gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:41

S105	4	p-gate and heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:45
S106	20195	jfet heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:45
S107	264	jfet and heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 12:45
S108	176	(InP InGaP GaInP Ingaas GaAs) and S107	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 12:45
S109	96	S108 and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 12:57
S110	11	"5161235" and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:24
S111	1	(US-20050167698-$).did.	US-PGPUB	OR	OFF	2005/11/09 15:24
S114	10	nishi.in. and (hemt hjfet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:35
S115	57	(WADA bito nishi).in. and (hemt hjfet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:35
S116	1403	(gaas gallium adj arsenide) near2 substrate and (hemt hjfet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:35
S117	82	barrier near4 (gainas ingaas) and (hfet hemt) and gate	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35

S118	14	"5548148"	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35
S119	12	S118 and p-type	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35
S120	125	(mesfet hemt) and recess with gate and n-type and p-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:35
S121	6	"4929985"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/09 15:35
S122	1608	(257/192,194,195,280,284).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/11/09 15:35
S123	724	barrier near4 (gaalas algaas)	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35
S124	72	barrier near4 (gainas ingaas) and hemt	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35
S125	11	"4849368"	US-PGPUB; USPAT	OR	OFF	2005/11/09 15:35